

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

Features

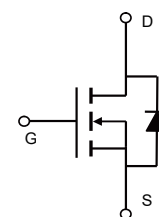
- Optimized body diode reverse recovery performance
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- RoHS&Halogen Free

Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)
- LLC Half-bridge



TO-220F



Schematic

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	600	V
Gate-Source Voltage ($V_{DS}=0V$) AC ($f>1\text{ Hz}$)	V_{GS}	± 30	V
Gate-Source Voltage ($V_{DS}=0V$) DC	V_{GS}	± 20	V
Continuous Drain Current at $T_c=25^\circ\text{C}$	$I_{D(DC)}$	51	A
Continuous Drain Current at $T_c=100^\circ\text{C}$	$I_{D(DC)}$	35.7	A
Pulsed drain current (Note 1)	$I_{DM(pluse)}$	153	A
Maximum Power Dissipation($T_c=25^\circ\text{C}$)	P_D	35.5	W
Derate above 25°C		0.23	W/ $^\circ\text{C}$
Single pulse avalanche energy (Note 2)	E_{AS}	576	mJ
Single pulse avalanche current (Note 2)	I_{AS}	12	A
Repetitive Avalanche energy, t_{AR} limited by T_{jmax} (Note 1)	E_{AR}	0.9	mJ
Drain Source voltage slope, $V_{DS} \leq 480\text{ V}$,	dv/dt	50	V/ns
Reverse diode dv/dt , $V_{DS} \leq 480\text{ V}, I_{SD} < I_D$	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+175	$^\circ\text{C}$

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	4.28	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	62	$^{\circ}\text{C}/\text{W}$

Table 3. Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =1mA	600			V
Zero Gate Voltage Drain Current(Tc=25℃)	I _{DSS}	V _{DS} =600V, V _{GS} =0V			10	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I _{DSS}	V _{DS} =600V, V _{GS} =0V			400	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =500μA	3.5	4.2	5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =25A		50	55	mΩ
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz		3836		pF
Output Capacitance	C _{oss}			155		pF
Reverse Transfer Capacitance	C _{rss}			8		pF
Total Gate Charge	Q _g	V _{DS} =480V, I _D =25A, V _{GS} =10V		58		nC
Gate-Source Charge	Q _{gs}			22		nC
Gate-Drain Charge	Q _{gd}			15		nC
Gate plateau voltage	V _{gp}			6.6		V
Intrinsic gate resistance	R _G	f = 1 MHz open drain		2		Ω
Switching times						
Turn-on Delay Time	t _{d(on)}	V _{DD} =380V, I _D =25A, R _G =1.7Ω, V _{GS} =10V		32		nS
Turn-on Rise Time	t _r			14		nS
Turn-Off Delay Time	t _{d(off)}			90		nS
Turn-Off Fall Time	t _f			9		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I _{SD}	T _c =25℃			51	A
Pulsed Source-drain current(Body Diode)	I _{SDM}				153	A
Forward On Voltage	V _{SD}	T _j =25℃, I _{SD} =51A, V _{GS} =0V		1.0	1.2	V
Reverse Recovery Time	t _{rr}	T _j =25℃, I _F =25A, di/dt=100A/μs		140		nS
Reverse Recovery Charge	Q _{rr}			0.63		uC
Peak Reverse Recovery Current	I _{rrm}			9		A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

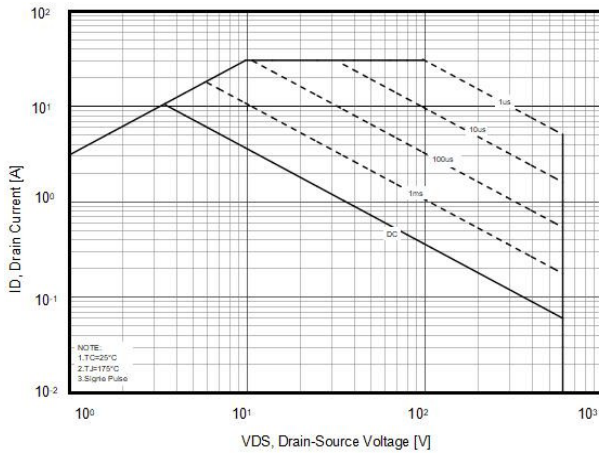
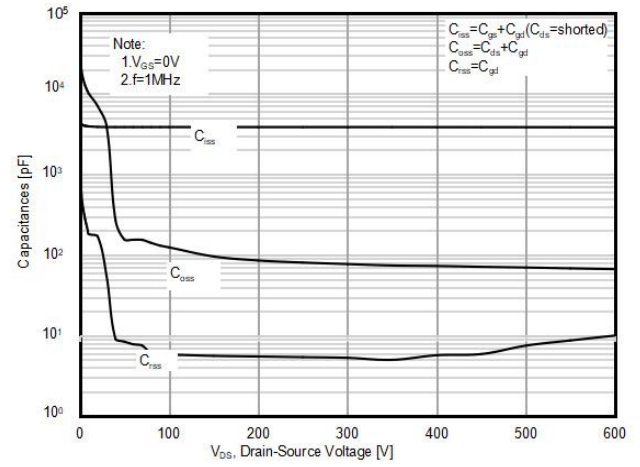
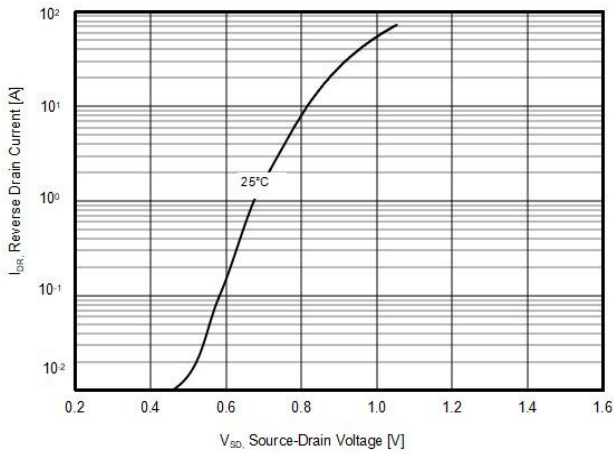
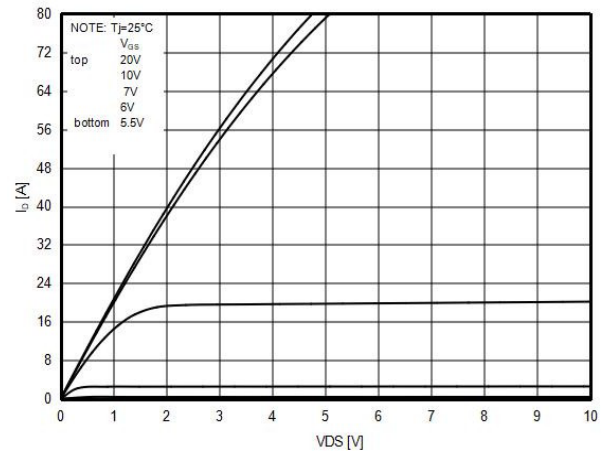
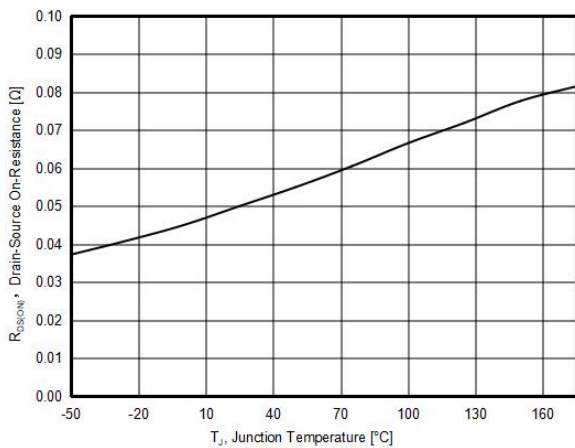
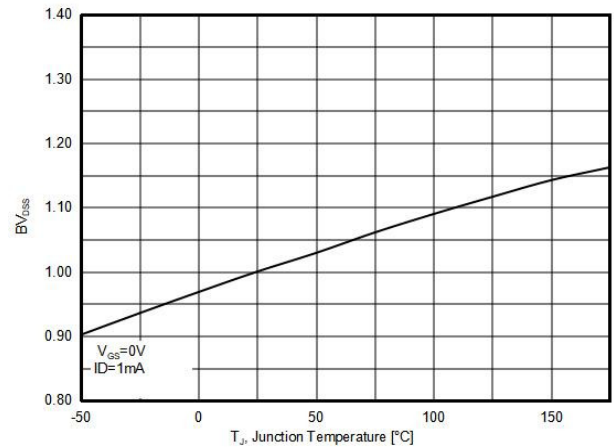
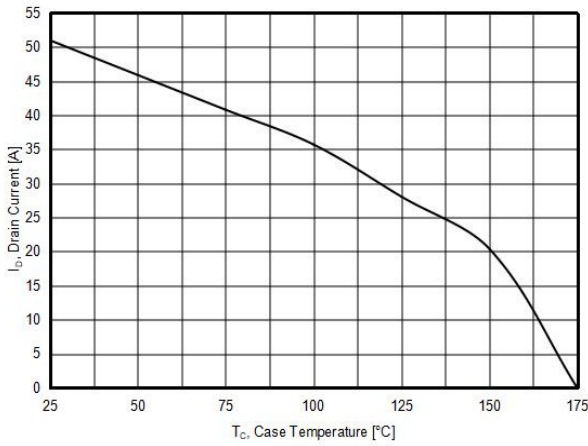
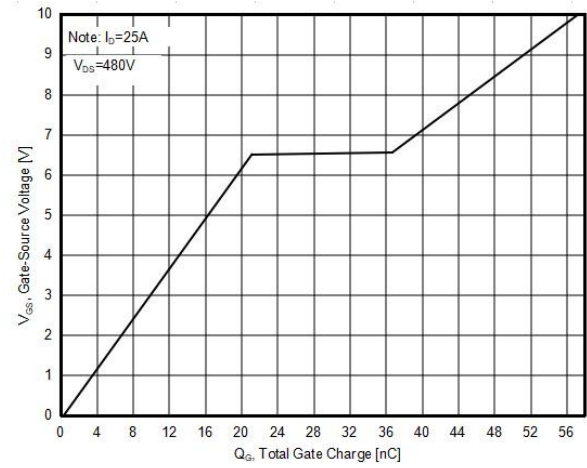
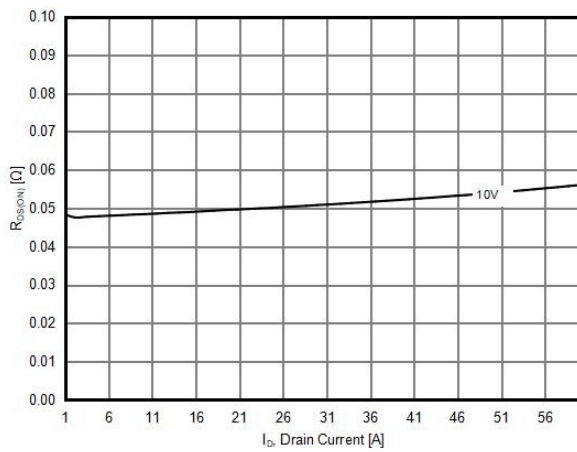
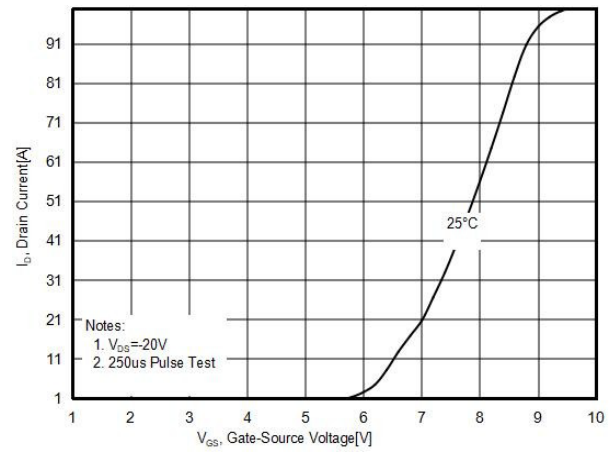
Figure1. Safe operating area

Figure2. Capacitance

Figure3. Source-Drain Diode Forward Voltage

Figure4. Output characteristics

Figure5. $R_{DS(ON)}$ vs Junction Temperature

Figure6. BV_{DSS} vs Junction Temperature


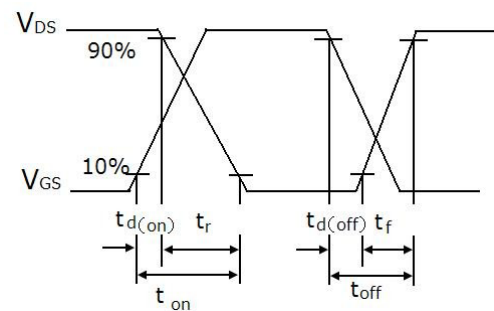
Figure7. Maximum I_D vs Junction Temperature

Figure8. Gate charge waveforms

Figure9. Static drain-source on resistance

Figure10. Transfer characteristics


Test circuit

1) Gate charge test circuit & Waveform



2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms

